

IGBT - Field Stop, Trench

75 A, 950 V

Product Preview

FGY75T95SQDT

Trench Field Stop 4th generation High Speed IGBT co-packaged with full current rated diode.

Features

- Maximum Junction Temperature : $T_J = 175^{\circ}\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(Sat)} = 1.69\text{ V (Typ.) @ } I_C = 75\text{ A}$
- Fast Switching
- Tighten Parameter Distribution
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Solar Inverter
- PFC
- DC/DC Converter

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector to Emitter Voltage	V_{CES}	950	V
Gate to Emitter Voltage	V_{GES}	± 20	V
Transient Gate to Emitter Voltage		± 30	V
Collector Current @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 100^{\circ}\text{C}$	I_C	150 75	A
Pulsed Collector Current (Note 1)	I_{LM}	300	A
Pulsed Collector Current (Note 2)	I_{CM}	300	A
Diode Forward Current @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 100^{\circ}\text{C}$	I_F	150 75	A
Pulsed Diode Forward Current (Note 2)	I_{FM}	300	A
Maximum Power Dissipation @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 100^{\circ}\text{C}$	P_D	434 217	W
Operating Junction / Storage Temperature Range	T_J, T_{STG}	-55 to $+175$	$^{\circ}\text{C}$
Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5 seconds	T_L	300	$^{\circ}\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

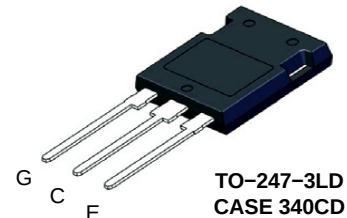
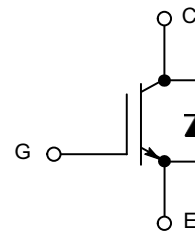
1. $V_{CC} = 700\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 300\text{ A}$, $R_G = 26\ \Omega$, Inductive Load, 100% Tested
2. Pulse width limited by max Junction temperature. Defined by design. Not subject to production test



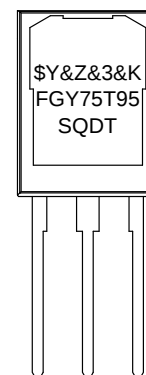
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75 A, 950 V
 $V_{CESat} = 1.69\text{ V (Typ.)}$



MARKING DIAGRAM



\$Y = ON Semiconductor Logo
&Z = Assembly Plant Code
&3 = Numeric Date Code
&K = 2-Digit Lot Traceability Code
FGY75T95SQDT = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

FGY75T95SQDT

ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
FGY75T95SQDT	FGY75T95SQDT	TO-247-3LD (Pb-Free)	30 Units / Rail

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction-to-case, for IGBT	$R_{\theta JC}$	0.35	°C/W
Thermal resistance junction-to-case, for Diode	$R_{\theta JC}$	0.23	°C/W
Thermal resistance junction-to-ambient	$R_{\theta JA}$	40	°C/W

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-emitter breakdown voltage, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	BV_{CES}	950			V
Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	$\frac{\Delta BV_{CES}}{\Delta T_J}$		0.96		V/°C
Collector-emitter cut-off current, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, V_{CE} = 950\text{ V}$	I_{CES}			250	μA
Gate leakage current, collector-emitter short-circuited	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}			±400	nA

ON CHARACTERISTICS

Gate-emitter threshold voltage	$V_{GE} = V_{CE}, I_C = 75\text{ mA}$	$V_{GE(th)}$	3.4	4.84	6.4	V
Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 75\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 75\text{ A}, T_J = 175^\circ\text{C}$	$V_{CE(sat)}$		1.69 2.25	2.11	V

DYNAMIC CHARACTERISTICS

Input capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{ies}		4770		pF
Output capacitance		C_{oes}		241		
Reverse transfer capacitance		C_{res}		19.7		
Gate charge total	$V_{CE} = 600\text{ V}, I_C = 75\text{ V}, V_{GE} = 15\text{ V}$	Q_g		137		nC
Gate to emitter charge		Q_{ge}		33.2		
Gate to collector charge		Q_{gc}		38.6		

SWITCHING CHARACTERISTICS, INDUCTIVE LOAD

Turn-on delay time	$T_J = 25^\circ\text{C}$ $V_{CC} = 600\text{ V}, I_C = 37.5\text{ A}$ $R_g = 4.7\ \Omega$ $V_{GE} = 15\text{ V}$ Inductive Load	$t_{d(on)}$		28.8		ns
Rise time		t_r		16.0		
Turn-off delay time		$t_{d(off)}$		104.0		
Fall time		t_f		30.4		
Turn-on switching loss		E_{on}		2.1		mJ
Turn-off switching loss		E_{off}		1.0		
Total switching loss		E_{ts}		3.2		

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Turn-on delay time	$T_J = 25^\circ\text{C}$ $V_{CC} = 600\text{ V}$, $I_C = 75\text{ A}$ $R_g = 4.7\ \Omega$ $V_{GE} = 15\text{ V}$ Inductive Load	$t_{d(on)}$		31.2		ns
Rise time		t_r		58.4		
Turn-off delay time		$t_{d(off)}$		96.0		
Fall time		t_f		65.6		
Turn-on switching loss		E_{on}		5.4		mJ
Turn-off switching loss		E_{off}		2.1		
Total switching loss		E_{ts}		7.6		
Turn-on delay time	$T_J = 175^\circ\text{C}$ $V_{CC} = 600\text{ V}$, $I_C = 37.5\text{ A}$ $R_g = 4.7\ \Omega$ $V_{GE} = 15\text{ V}$ Inductive Load	$t_{d(on)}$		28.8		ns
Rise time		t_r		17.6		
Turn-off delay time		$t_{d(off)}$		117.0		
Fall time		t_f		60.8		
Turn-on switching loss		E_{on}		4.1		mJ
Turn-off switching loss		E_{off}		1.7		
Total switching loss		E_{ts}		5.8		
Turn-on delay time	$T_J = 175^\circ\text{C}$ $V_{CC} = 600\text{ V}$, $I_C = 75\text{ A}$ $R_g = 4.7\ \Omega$ $V_{GE} = 15\text{ V}$ Inductive Load	$t_{d(on)}$		28.8		ns
Rise time		t_r		60.8		
Turn-off delay time		$t_{d(off)}$		106.0		
Fall time		t_f		92.8		
Turn-on switching loss		E_{on}		8.8		mJ
Turn-off switching loss		E_{off}		3.2		
Total switching loss		E_{ts}		12.0		

DIODE CHARACTERISTICS

Forward voltage	$I_F = 75\text{ A}$ $I_F = 75\text{ A}$, $T_J = 175^\circ\text{C}$	V_F		2.03 1.76	2.51	V
Reverse Recovery Energy	$T_J = 25^\circ\text{C}$ $V_R = 600\text{ V}$, $I_F = 37.5\text{ A}$ $dI_F/dt = 1000\text{ A}/\mu\text{s}$	E_{rec}		314		μJ
Reverse Recovery Time		t_{rr}		105		ns
Reverse Recovery Charge		Q_{rr}		1635		nC
Reverse Recovery Energy	$T_J = 25^\circ\text{C}$ $V_R = 600\text{ V}$, $I_F = 75\text{ A}$ $dI_F/dt = 1000\text{ A}/\mu\text{s}$	E_{rec}		2390		μJ
Reverse Recovery Time		t_{rr}		259		ns
Reverse Recovery Charge		Q_{rr}		7515		nC
Reverse Recovery Energy	$T_J = 175^\circ\text{C}$ $V_R = 600\text{ V}$, $I_F = 37.5\text{ A}$ $dI_F/dt = 1000\text{ A}/\mu\text{s}$	E_{rec}		454		μJ
Reverse Recovery Time		t_{rr}		148		ns
Reverse Recovery Charge		Q_{rr}		2436		nC

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Reverse Recovery Energy	$T_J = 175^\circ\text{C}$ $V_R = 600\text{ V}$, $I_F = 75\text{ A}$ $dI_F/dt = 1000\text{ A}/\mu\text{s}$	E_{rec}		2790		μJ
Reverse Recovery Time		t_{rr}		294		ns
Reverse Recovery Charge		Q_{rr}		9175		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

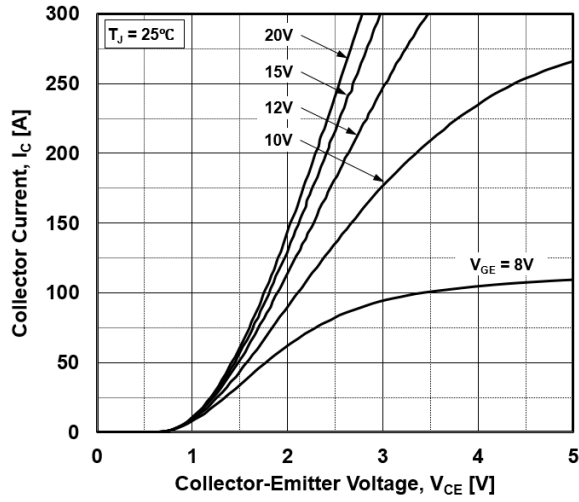


Figure 1. Typical Output Characteristics ($T_J = 25^\circ\text{C}$)

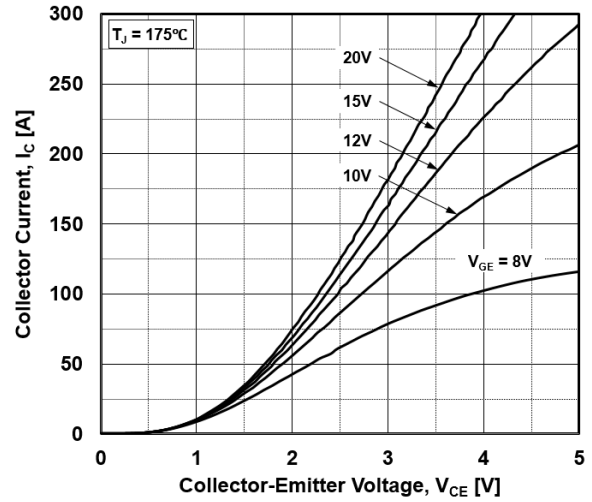


Figure 2. Typical Output Characteristics ($T_J = 175^\circ\text{C}$)

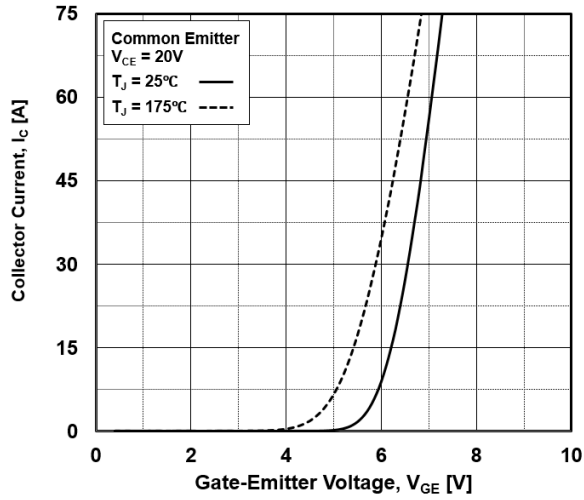


Figure 3. Transfer Characteristics

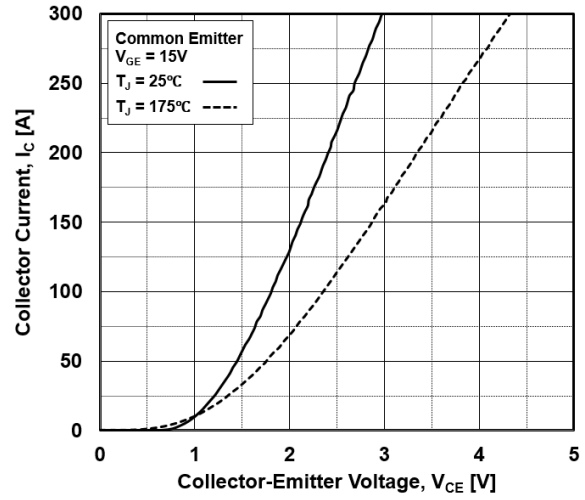


Figure 4. Typical Saturation Voltage Characteristics

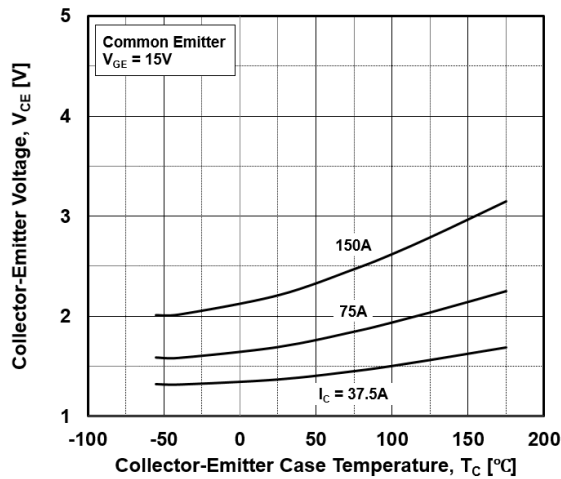


Figure 5. Saturation Voltage vs Case Temperature at Variant Current Level

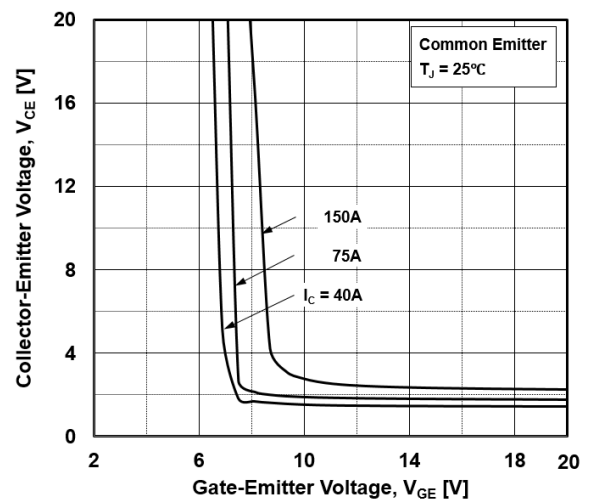


Figure 6. Saturation Voltage vs. V_{GE} ($T_J = 25^\circ\text{C}$)

TYPICAL CHARACTERISTICS

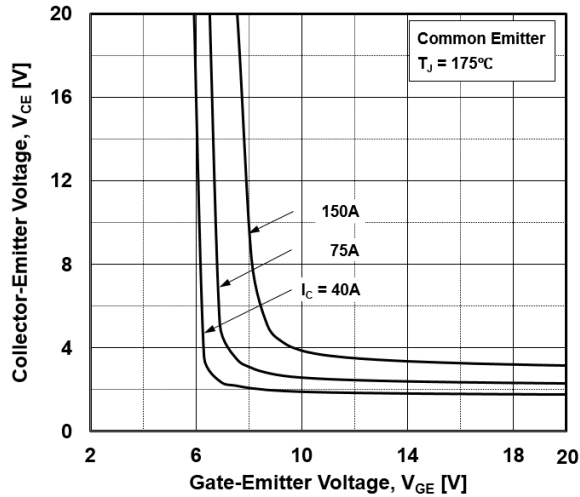


Figure 7. Saturation Voltage vs. V_{GE} ($T_J = 175^\circ\text{C}$)

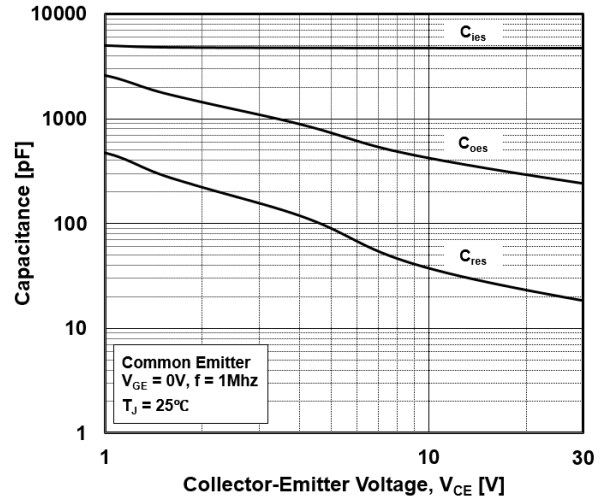


Figure 8. Capacitance Characteristics

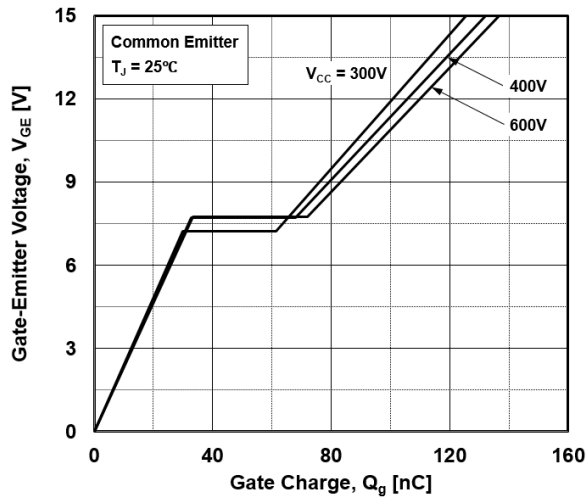


Figure 9. Gate Charge Characteristics ($T_J = 25^\circ\text{C}$)

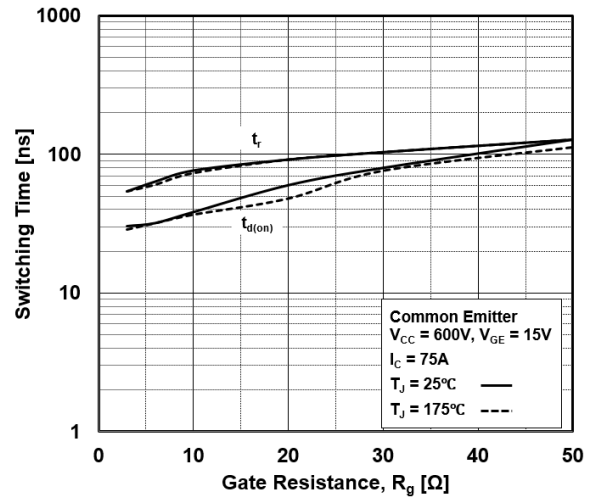


Figure 10. Turn-on Characteristics vs. Gate Resistance

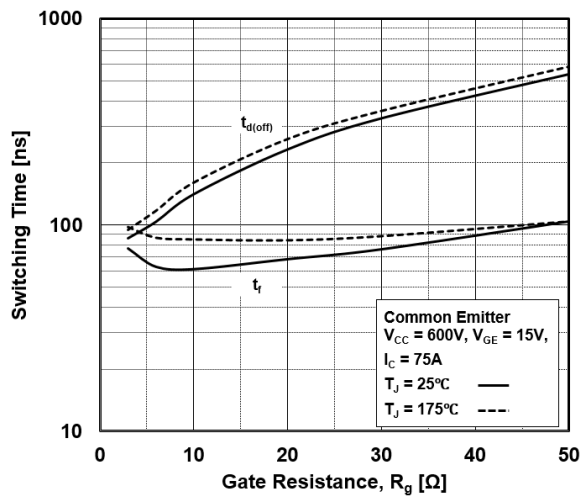


Figure 11. Turn-off Characteristics vs. Gate Resistance

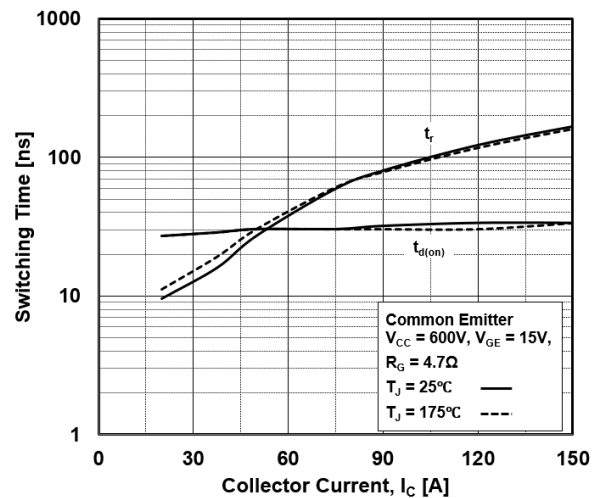


Figure 12. Turn-on Characteristics vs. Collector Current

TYPICAL CHARACTERISTICS

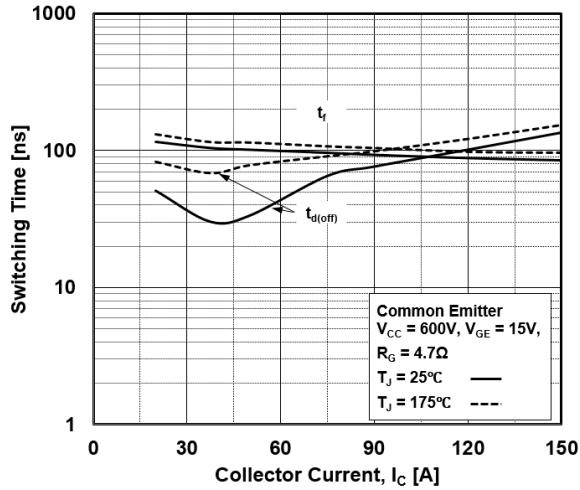


Figure 13. Turn-off Characteristics vs. Collector Current

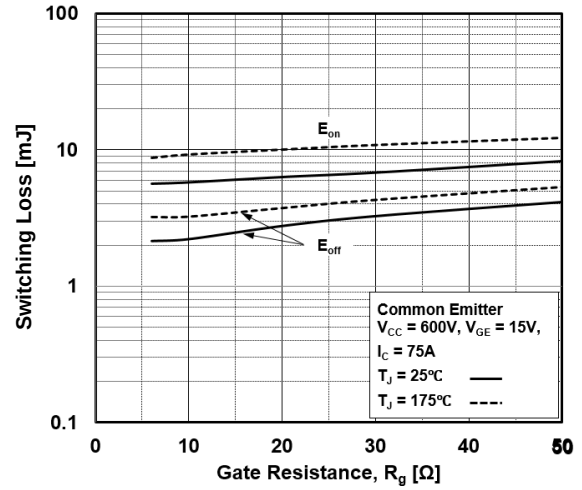


Figure 14. Switching Loss vs. Gate Resistance

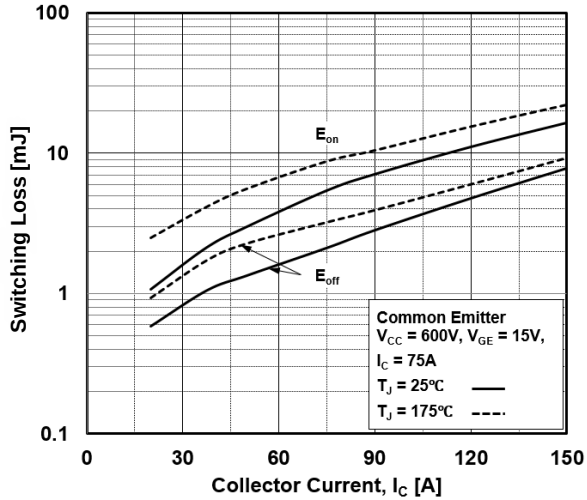


Figure 15. Switching Loss vs. Collector Current

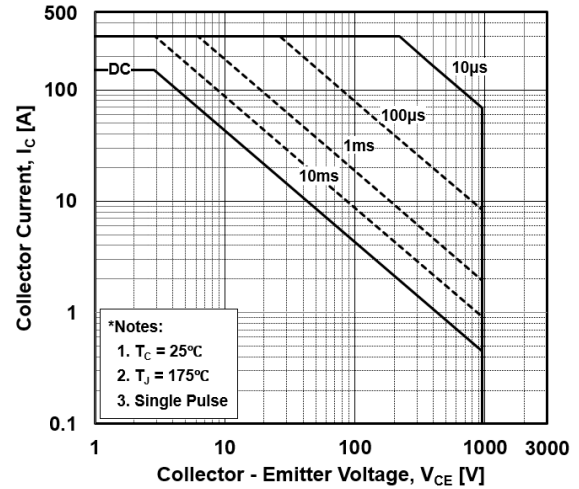


Figure 16. SOA Characteristics (FBSOA)

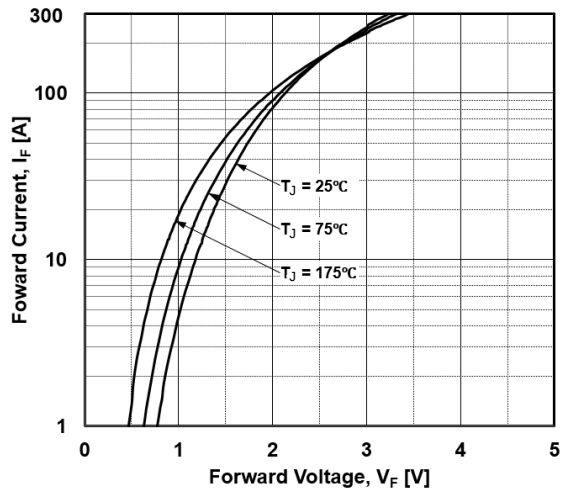


Figure 17. (Diode) Forward Characteristics vs (Normal I-V)

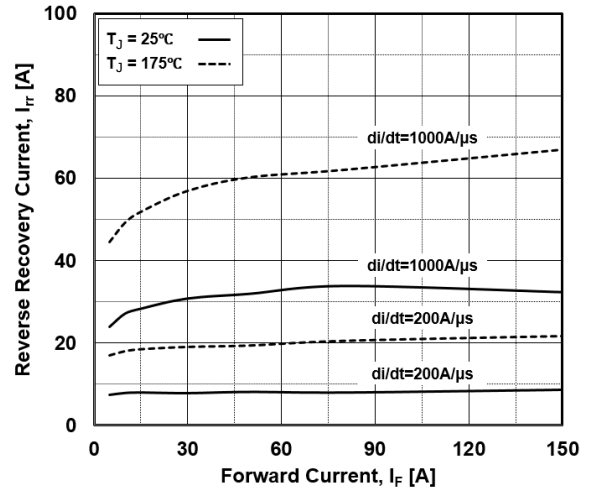


Figure 18. (Diode) Reverse Recovery Current

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TYPICAL CHARACTERISTICS

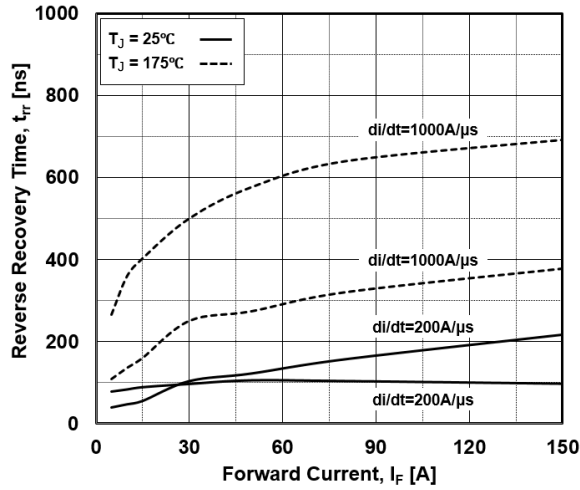


Figure 19. (Diode) Reverse Recovery Time

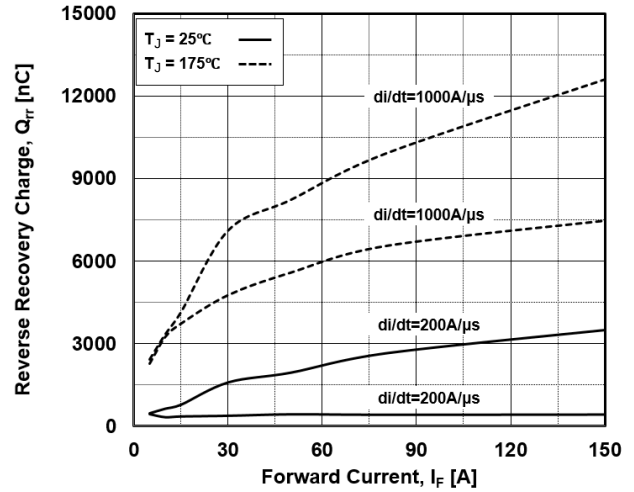


Figure 20. (Diode) Stored Charge

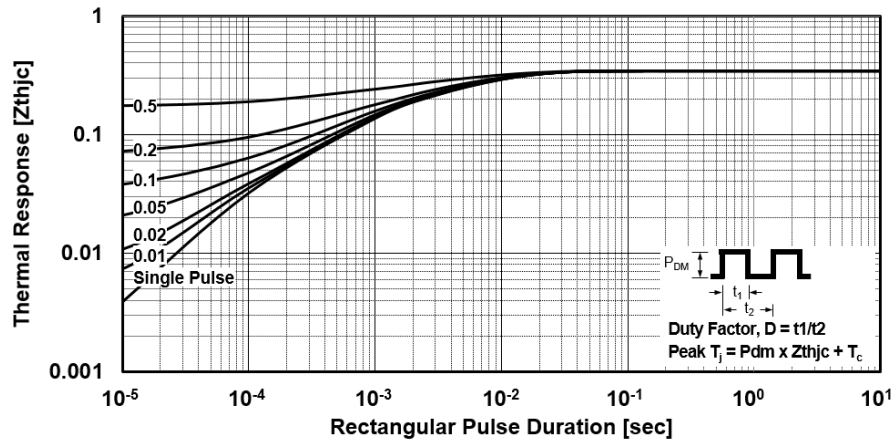


Figure 21. Transient Thermal Impedance of IGBT

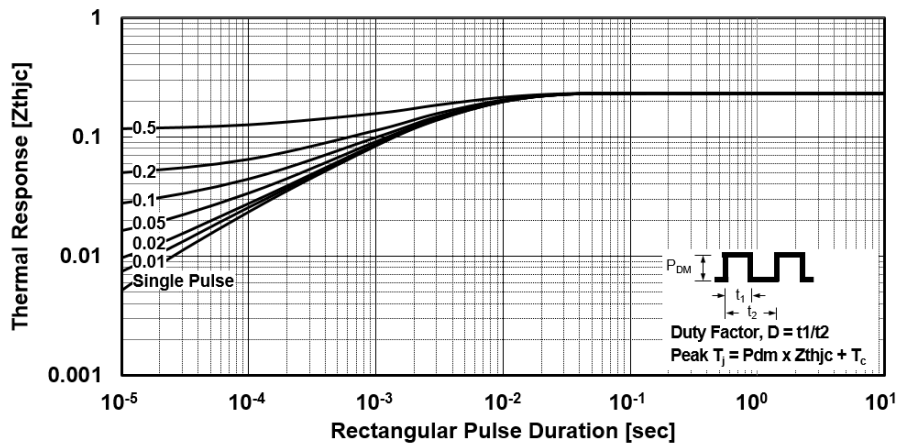
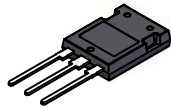


Figure 22. Transient Thermal Impedance of Diode

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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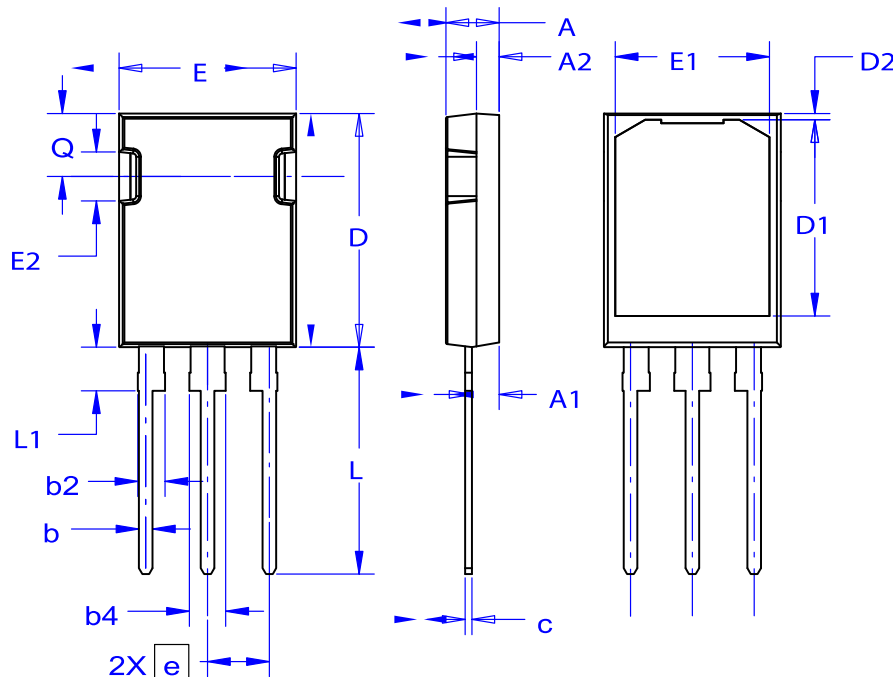


TO-247-3LD
CASE 340CD
ISSUE A

DATE 18 SEP 2018

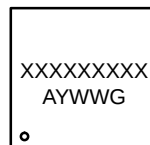
NOTES:

- A. THIS PACKAGE DOES NOT CONFORM TO ANY STANDARDS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- D. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.80	2.00	2.20
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.12	4.32	4.52
e	~	5.45	~
L	19.90	20.00	20.10
L1	3.69	3.81	3.93
Q	5.34	5.46	5.58
b	1.10	1.20	1.30
b2	2.10	2.24	2.39
b4	2.87	3.04	3.20
c	0.51	0.61	0.71
D1	16.63	16.83	17.03
D2	0.51	0.93	1.35
E1	13.40	13.60	13.80

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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